Fast Thyristor/Diode and Thyristor/Thyristor (MAGN-A-PAK™ Power Modules), 180 A

MAGN-A-PAK™

FEATURES

- Fast turn-off thyristor
- Fast recovery diode
- High surge capability
- Electrically isolated baseplate
- 3000 V_{RMS} isolating voltage
- Industrial standard package
- Lead (Pb)-free
- UL E78996 approved

Pb-free
RoHS COMPLIANT

DESCRIPTION

These series of MAGN-A-PAK™ modules are intended for applications such as self-commutated inverters, DC choppers, electronic welders, induction heating and others where fast switching characteristics are required.

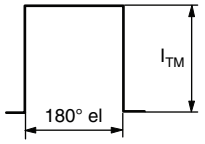
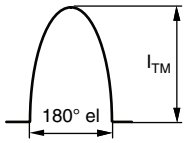
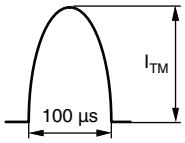
PRODUCT SUMMARY	
$I_{T(AV)}$	180 A

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$		180	A
	T_C	85	°C
$I_{T(RMS)}$		400	A
I_{TSM}	50 Hz	7130	
	60 Hz	7470	
I^2t	50 Hz	255	kA^2s
	60 Hz	232	
$I^2\sqrt{t}$		2550	$kA^2\sqrt{s}$
t_q		20/25	µs
t_{rr}		2	
V_{DRM}/V_{RRM}		Up to 1200	V
T_J	Range	- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{RRM}/V_{DRM}, MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM}/I_{DRM} MAXIMUM AT T_J = 125 °C mA
VSK.F180-	08	800	800	50
	12	1200	1200	

CURRENT CARRYING CAPABILITY

FREQUENCY							UNITS
50 Hz	370	530	565	800	2400	3150	A
400 Hz	435	650	670	1000	1540	2050	
2500 Hz	290	430	490	720	610	830	
5000 Hz	240	345	390	540	390	540	
10 000 Hz	170	270	290	390	-	-	
Recovery voltage V_r	50		50		50		V
Voltage before turn-on V_d	80 % V_{DRM}		80 % V_{DRM}		80 % V_{DRM}		
Rise of on-state current dI/dt	50		-		-		A/µs
Case temperature	85	60	85	60	85	60	°C
Equivalent values for RC circuit	10/0.47		10/0.47		10/0.47		Ω/µF

ON-STATE CONDUCTION

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave			180	A
					85	°C
Maximum RMS current	$I_{T(RMS)}$	As AC switch			400	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	7130	
		t = 8.3 ms			7470	
		t = 10 ms	100 % V_{RRM} reapplied		6000	
		t = 8.3 ms			6280	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		255	kA^2s
		t = 8.3 ms			232	
		t = 10 ms	100 % V_{RRM} reapplied		180	
		t = 8.3 ms			164	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			2550	$kA^2\sqrt{s}$
Low level value or threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.30	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.38	
Low level value on-state slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.90	mΩ
High level value on-state slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.71	
Maximum on-state voltage drop	V_{TM}	I_{pk} = 600 A, $T_J = T_J$ maximum, t_p = 10 ms sine pulse			1.84	V
Maximum holding current	I_H	T_J = 25 °C, I_T > 30 A			600	mA
Typical latching current	I_L	T_J = 25 °C, V_A = 12 V, Ra = 6 Ω, I_g = 1A			1000	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			K	J	
Maximum non-repetitive rate of rise	dI/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ ms, V_D = 80 % V_{DRM} T_J = 25 °C	800		A/µs
Maximum recovery time	t_{rr}	I_{TM} = 350 A, dI/dt = - 25 A/µs, V_R = 50 V, T_J = 25 °C	2		µs
Maximum turn-off time	t_q	I_{TM} = 750 A; T_J = 125 °C; dI/dt = - 25 A/µs; V_R = 50 V; dV/dt = 400 V/µs linear to 80 % V_{DRM}	20	25	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, exponential to 67 % V_{DRM}	1000	V/µs
RMS insulation voltage	V_{INS}	50 Hz, circuit to base, all terminals shorted, 25 °C, 1 s	3000	V
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	T_J = 125 °C, rated V_{DRM}/V_{RRM} applied	50	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	f = 50 Hz, d% = 50	60	W
Maximum peak average gate power	$P_{G(AV)}$	T_J = 125 °C, f = 50 Hz, d% = 50	10	
Maximum peak positive gate current	I_{GM}	T_J = 125 °C, $t_p \leq 5$ ms	10	A
Maximum peak negative gate voltage	- V_{GM}		5	V
Maximum DC gate current required to trigger	I_{GT}	T_J = 25 °C, V_{ak} 12 V, Ra = 6	200	mA
DC gate voltage required to trigger	V_{GT}		3	V
DC gate current not to trigger	I_{GD}	T_J = 125 °C, rated V_{DRM} applied	20	mA
DC gate voltage not to trigger	V_{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case per junction	R_{thJC}	DC operation	0.125	K/W
Maximuml thermal resistance, case to heatsink per module	R_{thCS}	Mounting surface, flat and greased	0.02	
Mounting torque ± 10 % — MAP to heatsink		Amounting compound is recommended. The torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Use of cable lugs is not recommended, busbar should be used and restrained during tightening. Threads must be lubricated with a compound.	4 to 6 (35 to 53)	N · m (lbf · in)
busbar to MAP				
Approximate weight			500	g
			17.8	oz.

ΔR_{thJC} CONDUCTION				
CONDUCTIONS ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.009	0.006	T_J = 125 °C	K/W
120°	0.010	0.011		
90°	0.014	0.015		
60°	0.020	0.020		
30°	0.032	0.033		

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

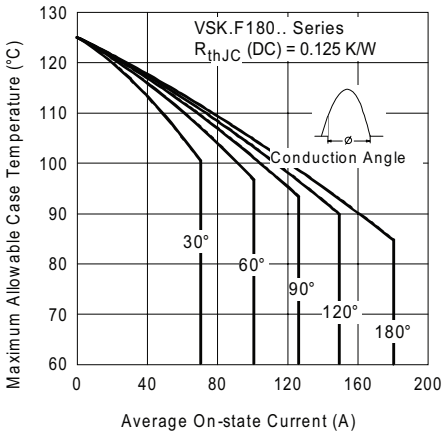


Fig. 1 - Current Ratings Characteristics

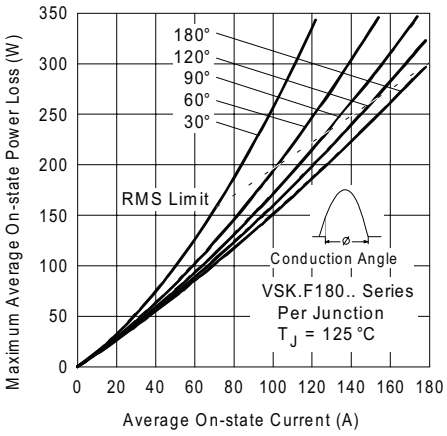


Fig. 3 - On-State Power Loss Characteristics

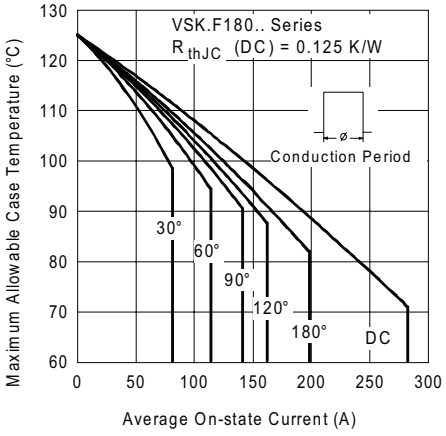


Fig. 2 - Current Ratings Characteristics

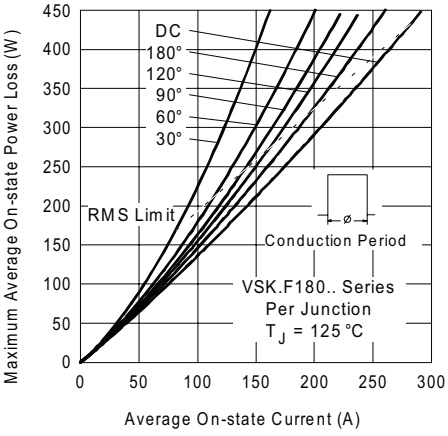


Fig. 4 - On-State Power Loss Characteristics

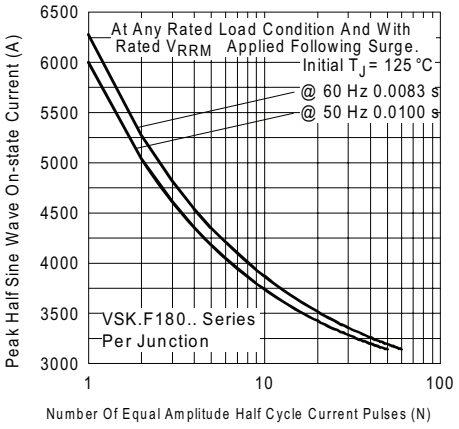


Fig. 5 - Maximum Non-Repetitive Surge Current

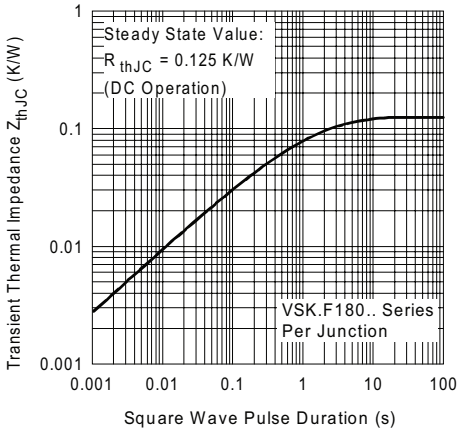


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

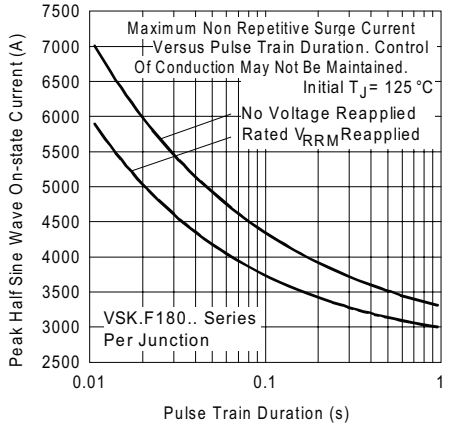


Fig. 6 - Maximum Non-Repetitive Surge Current

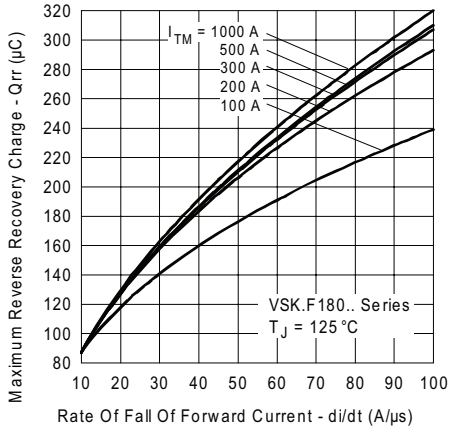


Fig. 9 - Reverse Recovery Charge Characteristics

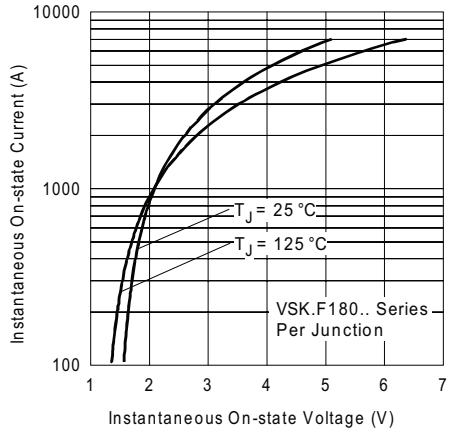


Fig. 7 - On-State Voltage Drop Characteristics

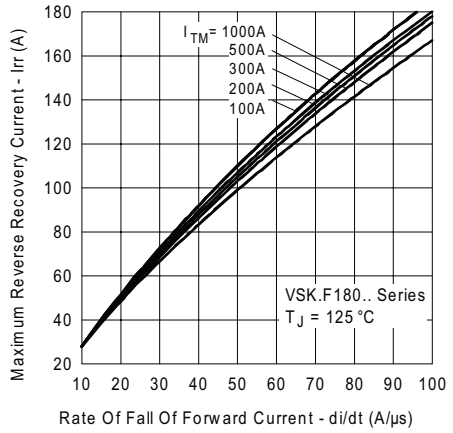


Fig. 10 - Reverse Recovery Current Characteristics

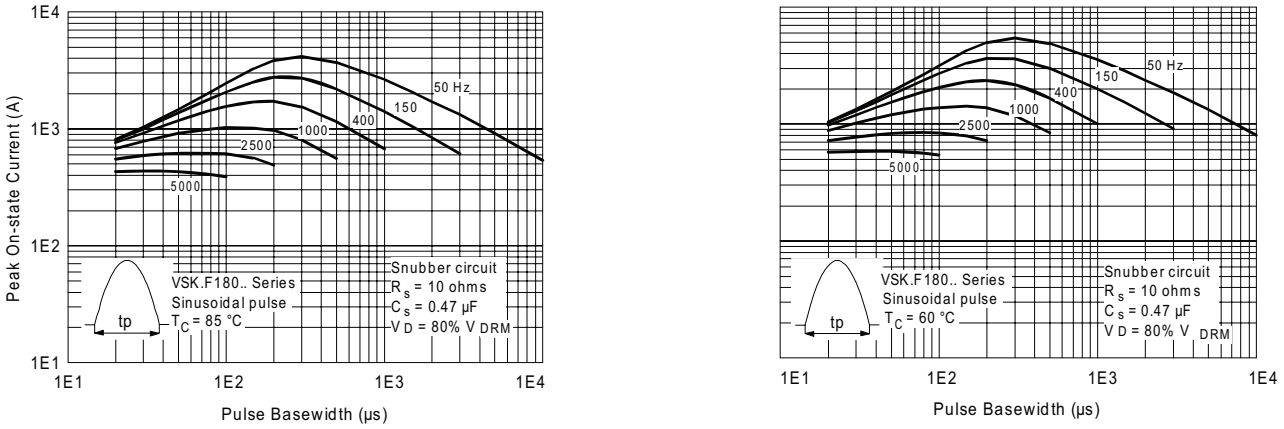


Fig. 11 - Frequency Characteristics

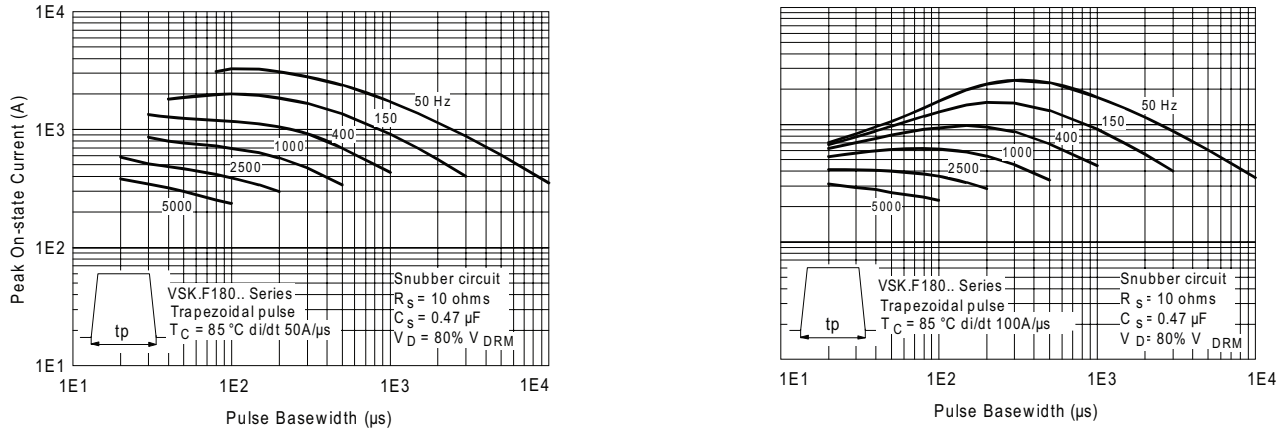


Fig. 12 - Frequency Characteristics

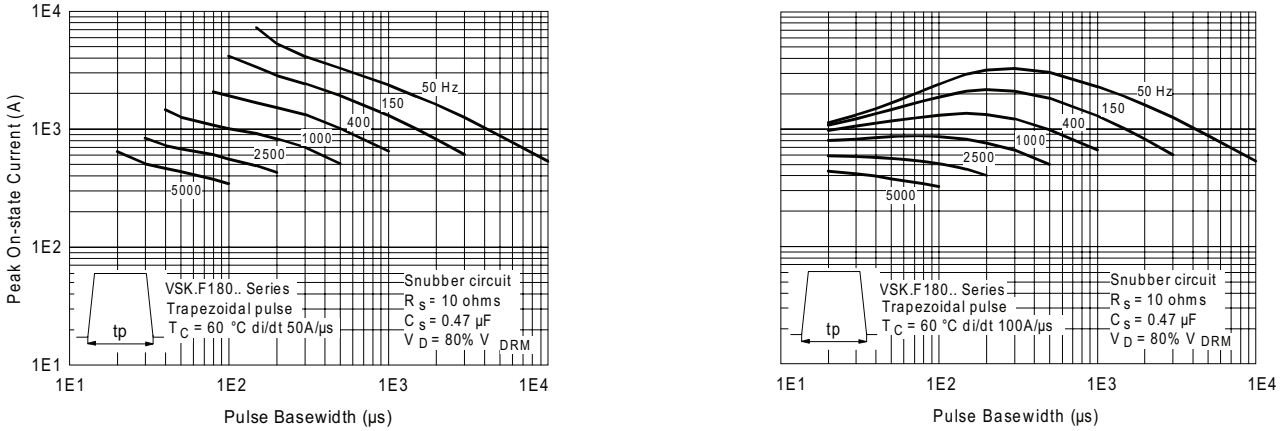


Fig. 13 - Frequency Characteristics

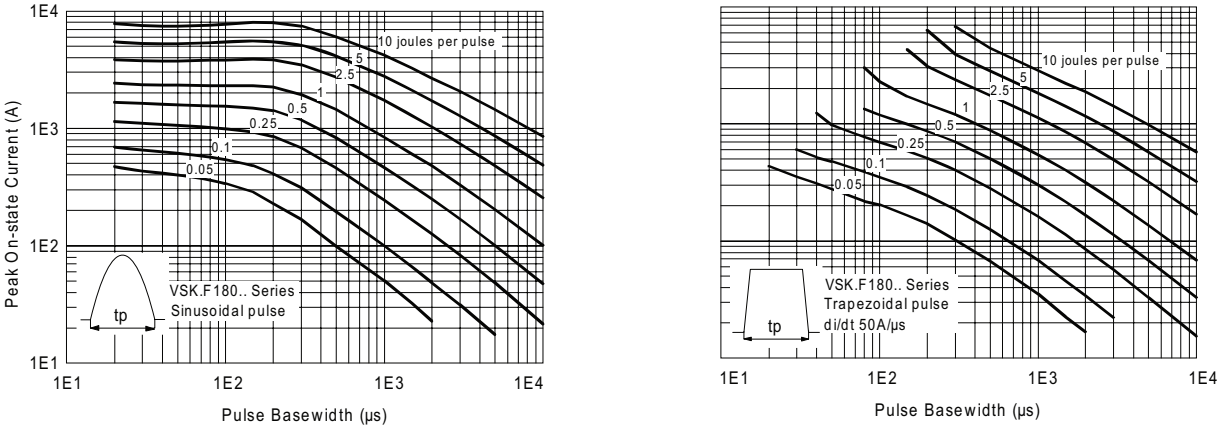


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

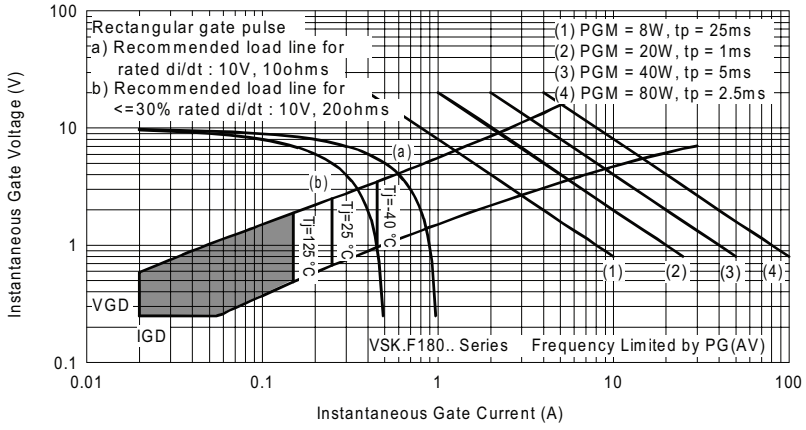


Fig. 15 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

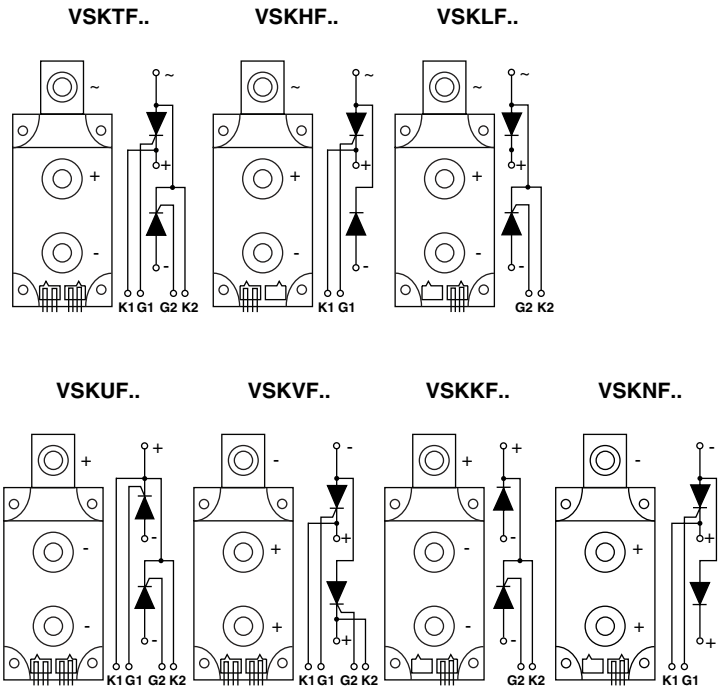
VSK	T	F	180	-	12	H	K	P
1	2	3	4		5	6	7	8

- 1 - Module type
- 2 - Circuit configuration
- 3 - Fast SCR
- 4 - Current rating: $I_{T(AV)}$ x 10 rounded
- 5 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 6 - dV/dt code: H ≤ 400 V/µs
- 7 - t_q code: K ≤ 20 µs
  J ≤ 25 µs
- 8 - P = Lead (Pb)-free

Note

- To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95086

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All product specifications and data are subject to change without notice.

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